

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1211	(optical adj print\$6 adj head)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 09:06
L2	564	1 same (led (light adj emit\$6))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 09:12
L3	125	2 same lens	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 09:12
L4	20	3 same (photosensitive drum electrostatic)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 09:12
L5	258	(optical adj print\$6 adj head)	US-PGPUB; USPAT	OR	ON	2005/05/05 09:10
L6	146	5 same (led (light adj emit\$6))	US-PGPUB; USPAT	OR	ON	2005/05/05 09:10
L7	87	6 same (photosensitive drum electrostatic lens)	US-PGPUB; USPAT	OR	ON	2005/05/05 11:35
L8	776	1 and (led (light adj emit\$6))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 09:12
L9	236	8 and lens	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 09:12
L10	55	9 and (photosensitive drum electrostatic)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 09:13
L11	52	(rod adj lens adj array) and (photosensitive adj drum) and (transfer adj roller)	US-PGPUB; USPAT	OR	ON	2005/05/05 10:43
L12	16	(rod adj lens adj array) same clamp same base same hold\$6	US-PGPUB; USPAT	OR	ON	2005/05/05 11:36
S1	2	jp-10063807-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/05/03 09:13
S2	1524	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) same (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon)) same ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	US-PGPUB; USPAT	OR	ON	2005/05/04 09:37

S3	1406	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 09:38
S4	4	S3 and (optical adj print\$6 adj head)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 09:06
S5	3	S2 and (optical adj print\$6 adj head)	US-PGPUB; USPAT	OR	ON	2005/05/05 09:10
S6	6037	257/81.ccls. 257/82.ccls. 257/84.ccls. 257/93.ccls. 257/98.ccls. 257/99.ccls. 257/693.ccls. 257/700.ccls. 257/701.ccls. 257/783.ccls.	US-PGPUB; USPAT	OR	ON	2005/05/03 09:28
S7	148	S2 and S6	US-PGPUB; USPAT	OR	ON	2005/05/03 09:40
S8	103	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) with (adhe\$8 near2 (semiconductor amorphous polycrystalline polysilicon)) with ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) near2 (semiconductor device silicon))	US-PGPUB; USPAT	OR	ON	2005/05/03 15:21
S9	238	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 near2 (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 09:32
S10	112	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 near2 (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) near2 (semiconductor device silicon))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 15:33

S11	1	"6576933".pn.	US-PGPUB; USPAT	OR	OFF	2005/05/03 15:25
S12	1	"20020030197".pn.	US-PGPUB; USPAT	OR	OFF	2005/05/03 15:29
S13	2	jp-07065348-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/05/03 15:29
S14	212	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) same (adhe\$8 with (amorphous polycrystalline polysilicon)) same ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	US-PGPUB; USPAT	OR	ON	2005/05/04 09:39
S15	150	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with (amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 09:39
S16	67	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) same (adhe\$8 near4 (amorphous polycrystalline polysilicon)) same ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	US-PGPUB; USPAT	OR	ON	2005/05/04 09:39
S17	56	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 near4 (amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 11:35
S18	6	jp-02028315-\$.did. jp-63226914-\$.did. jp-11031828-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/05/04 11:36